



Lead (Pb) Free Product – RoHS Compliant

LED910-66-60 epoxy lens type Infrared illuminator

L910-66-60 is a wide viewing and extremely high output power illuminator assembled with a total of 60 high efficiency AlGaAs diode chips, mounted on a metal stem TO-66 with AlN ceramics and covered with double coated clear silicone and epoxy resin. These devices are designed for high current operation with proper heat sinking to improve thermal conductive efficiency.

◆ Features

- 1) high reliability
- 2) compact(TO-66)package
- 3) high output power at 910nm

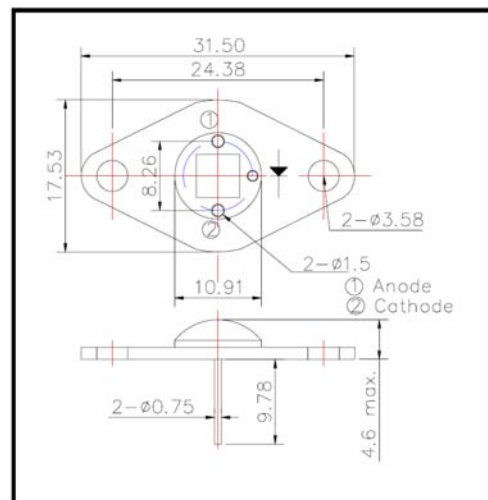
◆ Applications

- 1) For IR search light
- 2) For CCD lighting

◆ Specifications

- 1) Product name IR illuminator
- 2) Spec. No. L910-66-60
- 3) Chip
 - (1) Material AlGaAs
 - (2) Peak wavelength 910nm
- 4) Package
 - (1) Stem TO-66 stem with AlN
 - (2) Lens Clear silicone and epoxy lens

◆ Outer dimension (Unit:mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	7.5	W	T _a =25°C
Forward Current	I _F	1.0	A	T _a =25°C
Pulse Forward Current	I _{FP}	2.5	A	T _a =25°C
Reverse Voltage	V _R	50	V	T _a =25°C
Operating Temperature	T _{OPR}	-30 ~ +80	°C	
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	240	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=1us.

‡Soldering condition : Soldering condition must be completed within 3 seconds at 260°C

◆ Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =800mA		7.0		V
Reverse Voltage	V _R	I _R =10uA	50			V
Total Radiated Power	P _o	I _F =800mA		600		mW
Total Radiated Power	P _o	I _{FP} =5A		3500		mW
Radiant Intensity	I _E	I _F =800mA		200		mW/sr
Peak Wavelength	λ _P	I _F =800mA	900	910	930	nm
Half Width	Δλ	I _F =800mA		40		nm
Viewing Half Angle	θ _{1/2}	I _F =800mA		±60		deg.

‡Heat sink is required thermal resistance <8K/W